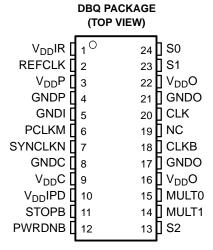


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DIRECT RAMBUS™ CLOCK GENERATOR

FEATURES

- 400-MHz Differential Clock Source for Direct Rambus[™] Memory Systems for an 800-MHz Data Transfer Rate
- Fail-Safe Power Up Initialization
- Synchronizes the Clock Domains of the Rambus Channel With an External System or Processor Clock
- Three Power Operating Modes to Minimize Power for Mobile and Other Power-Sensitive Applications
- Operates From a Single 3.3-V Supply and 120 mW at 300 MHz (Typ)
- Packaged in a Shrink Small-Outline Package (DBQ)
- Supports Frequency Multipliers: 4, 6, 8, 16/3
- No External Components Required for PLL
- Supports Independent Channel Clocking
- Spread Spectrum Clocking Tracking Capability to Reduce EMI
- Designed for Use With TI's 133-MHz Clock Synthesizers CDC924 and CDC921
- Cycle-Cycle Jitter Is Less Than 50 ps at 400 MHz
- Certified by Gigatest Labs to Exceed the Rambus DRCG Validation Requirement
- Supports Industrial Temperature Range of -40°C to 85°C



NC - No internal connection

DESCRIPTION

The Direct Rambus clock generator (DRCG) provides the necessary clock signals to support a Direct Rambus memory subsystem. It includes signals to synchronize the Direct Rambus channel clock to an external system or processor clock. It is designed to support Direct Rambus memory on a desktop, workstation, server, and mobile PC motherboards. DRCG also provides an off-the-shelf solution for a broad range of Direct Rambus memory applications.

The DRCG provides clock multiplication and phase alignment for a Direct Rambus memory subsystem to enable synchronous communication between the Rambus channel and ASIC clock domains. In a Direct Rambus memory subsystem, a system clock source provides the REFCLK and PCLK clock references to the DRCG and memory controller, respectively. The DRCG multiplies REFCLK and drives a high-speed BUSCLK to RDRAMs and the memory controller. Gear ratio logic in the memory controller divides the PCLK and BUSCLK frequencies by ratios M and N such that PCLKM = SYNCLKN, where SYNCLK = BUSCLK/4. The DRCG detects the phase difference between PCLKM and SYNCLKN and adjusts the phase of BUSCLK such that the skew between PCLKM and SYNCLKN is minimized. This allows data to be transferred across the SYNCLK/PCLK boundary without incurring additional latency.

A

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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User control is provided by multiply and mode selection terminals. The multiply terminals provide selection of one of four clock frequency multiply ratios, generating BUSCLK frequencies ranging from 267 MHz to 400 MHz with clock references ranging from 33 MHz to 100 MHz. The mode select terminals can be used to select a bypass mode where the frequency multiplied reference clock is directly output to the Rambus channel for systems where synchronization between the Rambus clock and a system clock is not required. Test modes are provided to bypass the PLL and output REFCLK on the Rambus channel and to place the outputs in a high-impedance state for board testing.

The CDCR83A has a fail-safe power up initialization state-machine which supports proper operation under all power up conditions.

The CDCR83A is characterized for operation over free-air temperatures of -40°C to 85°C.

FUNCTIONAL BLOCK DIAGRAM PWRDWNB S0 S2 **STOPB Test MUX Bypass MUX ByPCLK PLLCLK** CLK PLL Phase **CLKB REFCLK** В Aligner **PACLK** $\varphi_{\boldsymbol{D}}$ 2 PCLKM | SYNCLKN **MULTO**

FUNCTION TABLE(1)

MODE	S0	S1	S2	CLK	CLKB
Normal	0	0	0	Phase aligned clock	Phase aligned clock B
Bypass	1	0	0	PLLCLK	PLLCLKB
Test	1	1	0	REFCLK	REFCLKB
Output test (OE)	0	1	Х	Hi-Z	Hi-Z
Reserved	0	0	1	_	-
Reserved	1	0	1	_	-
Reserved	1	1	1	Hi-Z	Hi-Z

(1) X = don't care, Hi-Z = high impedance

MULT1



TERMINAL FUNCTIONS

TERMIN	NAL		DECODINE
NAME	NO.	I/O	DESCRIPTION
CLK	20	0	Output clock
CLKB	18	0	Output clock (complement)
GNDC	8		GND for phase aligner
GNDI	5		GND for control inputs
GNDO	17, 21		GND for clock outputs
GNDP	4		GND for PLL
MULT0	15	ı	PLL multiplier select
MULT1	14	ı	PLL multiplier select
NC	19		Not used
PCLKM	6	I	Phase detector input
PWRDNB	12	I	Active low power down
REFCLK	2	ı	Reference clock
S0	24	ı	Mode control
S1	23	I	Mode control
S2	13	I	Mode control
STOPB	11	ı	Active low output disable
SYNCLKN	7	ı	Phase detector input
V _{DD} C	9		V _{DD} for phase aligner
V _{DD} IPD	10		Reference voltage for phase detector inputs and STOPB
V _{DD} IR	1		Reference voltage for REFCLK
V _{DD} O	16, 22		V _{DD} for clock outputs
$V_{DD}P$	3		V _{DD} for PLL



PLL DIVIDER SELECTION

Table 1 lists the supported REFCLK and BUSCLK frequencies. Other REFCLK frequencies are permitted, provided that (267 MHz < BUSCLK < 400 MHz) and (33 MHz < REFCLK < 100 MHz).

Table 1. REFCLK and BUSCLK Frequencies

MULT0	MULT1	REFCLK (MHz)	MULTIPLY RATIO	BUSCLK ⁽¹⁾ (MHz)
0	0	67	4	267
0	1	50	6	300
0	1	67	6	400
1	1	33	8	267
1	1	50	8	400
1	0	67	16/3	356

⁽¹⁾ BUSCLK will be undefined until a valid reference clock is available at REFCLK. After applying REFCLK, the PLL requires stabilization time to achieve phase lock.

Table 2. Clock Output Driver States

STATE	PWRDNB	STOPB	CLK	CLKB
Powerdown	0	Х	GND	GND
CLK stop	1	0	V _{X, STOP}	V _{X, STOP}
Normal	1	1	PACLK/PLLCLK/REFCLK ⁽¹⁾	PACLKB/PLLCLKB/REFCLKB

⁽¹⁾ Depending on the state of S0, S1, and S2

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)(1)

		UNIT
V_{DD}	Supply voltage range (2)	−0.5 V to 4 V
Vo	Output voltage range at any output terminal	-0.5 V to V _{DD} + 0.5 V
VI	Input voltage rangeat any input terminal	-0.5 V to V _{DD} + 0.5 V
	Continuous total power dissipation	See Dissipation Rating Table
T _A	Operating free-air temperature range	−40°C to 85°C
T _{stg}	Storage temperature range	−65°C to 150°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATINGS

PACKAGE	T _A ≤ 25°C	DERATING FACTOR	T _A = 70°C	T _A = 85°C
	POWER RATING	ABOVE T _A = 25°C ⁽¹⁾	POWER RATING	POWER RATING
DBQ	1400 mW	11 mW/°C	905 mW	740 mW

⁽¹⁾ This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

⁽²⁾ All voltage values are with respect to the GND terminals.



RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage	3.135	3.3	3.465	V
V_{IH}	High-level input voltage (CMOS)	$0.7 \times V_{DD}$			V
V_{IL}	Low-level input voltage (CMOS)			$0.3 \times V_{DD}$	V
	Initial phase error at phase detector inputs (required range for phase aligner)	$-0.5 \times t_{c(PD)}$		$0.5 \times t_{c(PD)}$	V
V_{IL}	REFCLK low-level input voltage			$0.3 \times V_{DD}IR$	V
V _{IH}	REFCLK high-level input voltage	$0.7 \times V_{DD}IR$			V
V_{IL}	Input signal low voltage (STOPB)		0.	$3 \times V_{DD}IPD$	V
V _{IH}	Input signal high voltage (STOPB)	$0.7 \times V_{DD}IPD$			V
	Input reference voltage for (REFCLK) (VDDIR)	1.235		3.465	V
	Input reference voltage for (PCLKM and SYSCLKN) (VDDIPD)	1.235		3.465	V
I _{OH}	High-level output current			-16	mA
I _{OL}	Low-level output current			16	mA
T _A	Operating free-air temperature	-40		85	°C

TIMING REQUIREMENTS

		МІ	N MAX	UNIT
t _{c(in)}	Input cycle time	1	0 40	ns
	Input cycle-to-cycle jitter		250	ps
	Input duty cycle over 10,000 cycles	40	% 60%	
f_{mod}	Input frequency modulation,	3	33	kHz
	Modulation index, nonlinear maximum 0.5%		0.6%	
	Phase detector input cycle time (PCLKM and SYNCLKN)	3	30 100	ns
SR	Input slew rate		1 4	V/ns
	Input duty cycle (PCLKM and SYNCLKN)	25	% 75%	



ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETE	R	TEST COND	TEST CONDITIONS ⁽¹⁾			MAX	UNIT
V _{O(STOP)}	Output voltage during	CLK Stop (STOPB = 0)	See Figure 1		1.1		2	
$V_{O(X)}$	Output crossing-point	voltage	See Figure 1 and Fi	1.3		1.8	V	
Vo	Output voltage swing		See Figure 1		0.4		0.6	V
V _{IK}	Input clamp voltage		VDD = 3.135 V,	$I_{I} = -18 \text{ mA}$			-1.2	V
			See Figure 1				2	
V _{OH}	High-level output volta	age	V_{DD} = min to max,	$I_{OH} = -1 \text{ mA}$	V _{DD} - 0.1			V
			V _{DD} = 3.135 V,	$I_{OH} = -16 \text{ mA}$	2.4			
			See Figure 1		1			
V _{OL}	Low-level output volta	ige	V_{DD} = min to max,	$I_{OH} = 1 \text{ mA}$			0.1	V
			$V_{DD} = 3.135 V,$	$I_{OH} = 16 \text{ mA}$			0.5	
			$V_{DD} = 3.135 \text{ V},$	V _O = 1 V	-32	-52		
I _{OH}	High-level output curre	ent	V _{DD} = 3.3 V,	V _O = 1.65 V		– 51		mA
			V _{DD} = 3.465 V,	V _O = 3.135 V		-14.5	-21	
			V _{DD} = 3.135 V,	V _O = 1.95 V	43	61.5		
I _{OL}	Low-level output curre	ent	$V_{DD} = 3.3 \text{ V},$	V _O = 1.65 V		65		mA
			$V_{DD} = 3.465 V,$	$V_0 = 0.4 \ V$		25.5	36	
l _{oz}	High-impedance-state	output current	S0 = 0, S1 = 1				±10	μΑ
I _{OZ(STOP)}	High-impedance-state CLK stop	output current during	Stop = 0, $V_O = GND$	or V _{DD}			±100	μΑ
I _{OZ(PD)}	High-impedance-state power-down state	output current in	PWRDNB = 0, V _O =	-10		100	μΑ	
	High-level input	REFCLK, PCLKM, SYNCLKN, STOPB	V 0.405.V				10	
I _{IH}	current	PWRDNB, S0, S1, S2, MULT0, MULT1	$V_{DD} = 3.465 \text{ V}, \qquad \qquad V_{I} = V_{DD}$				10	μΑ
	Low-level input	REFCLK, PCLKM, SYNCLKN, STOPB	V 0.405.V				-10	
I _{IL}	current	PWRDNB, S0, S1, S2, MULT0, MULT1	$V_{DD} = 3.465 \text{ V},$	V _I = 0			-10	μΑ
7	Outrout improduces	High state	R _I at I _O - 14.5 mA to	−16.5 mA	15	35	50	0
Z _O	Output impedance	Low state	R _I at I _O 14.5 mA to	16.5 mA	11	17	35	Ω
	Defenses	VIDDID VIDDIDD	V 0.405.V	PWRDNB = 0			50	μΑ
	Reference current	VDDIR, VDDIPD	$V_{DD} = 3.465 \text{ V}$	PWRDNB = 1			0.5	mA
C _I	Input capacitance		$V_I = V_{DD}$ or GND			2		рF
Co	Output capacitance		$V_O = V_{DD}$ or GND		3		pF	
I _{DD(PD)}	Supply current in pwo	er-down state	REFCLK = 0 MHz to 100 MHz, PWDNB = 0, STOPB = 1				100	μΑ
I _{DD(CLKSTOP)}	Supply current in CLK	stop state	BUSCLK configured	for 400 MHz			30	mA
I _{DD(NORMAL)}	Supply current in norr	nal state	BUSCLK = 400 MH	Z			70	mA

 V_{DD} refers to any of the following; $V_{DD},\,V_{DD}IPD,\,V_{DD}IR,\,V_{DD}O,\,V_{DD}C,$ and $V_{DD}P$ All typical values are at V_{DD} = 3.3 V, T_A = 25°C.



SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMI	ETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{c(out)}	Clock output cycle time				2.5		3.75	ns
			267 MHz				80	
	Total cycle jitter over 1, 2,	Infinite and stopped	300 MHz	Can Figure 2			70	20
t _(jitter)	3, 4, 5, or 6 clock cycles	phase alignment	356 MHz	See Figure 3			60	ps
			400 MHz				50	
t _(phase)	Phase detector phase error	for distributed loop		Static phase error ⁽²⁾	-100		100	ps
t _(phase, SSC)	PLL output phase error who	Dynamic phase error ⁽²⁾	-100		100	ps		
	Output duty cycle over 10,0	See Figure 4	45%		55%			
			267 MHz				80	
	Output cycle-to-cycle duty	Infinite and stopped	300 MHz	See Figure 5			70	
t _(DC, err)	cycle error	phase alignment	356 MHz				60	ps
			400 MHz				50	
t _r , t _f	Output rise and fall times (r voltage)	measured at 20%-80%	See Figure 7	160		400	ps	
Δt	Difference between rise and (20%–80%) t _f t _r	d fall times on a single	device	See Figure 7			100	ps

⁽¹⁾ All typical values are at V_{DD} = 3.3 V, T_A = 25°C. (2) Assured by design

STATE TRANSITION LATENCY SPECIFICATIONS

	PARAMETER	FROM	то	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _(powerup)	Delay time, PWRDNB↑ to CLK/CLKB output settled (excluding t _(DISTLOCK))	Powerdown	Normal	See Figure 8			3	ma
	Delay time, PWRDNB↑ to internal PLL and clock are on and settled	Powerdown	Nomai				3	ms
t _(VDDpowerup)	Delay time, power up to CLK/CLKB output settled		Normal	See Figure 8			3	
	Delay time, power up to internal PLL and clock are on and settled	V _{DD}	Nomai				3	ms
t _(MULT)	MULT0 and MULT1 change to CLK/CLKB output resettled (excluding t _(DISTLOCK))	Normal	Normal	See Figure 9			1	ms
t _(CLKON)	STOPB [↑] to CLK/CLKB glitch-free clock edges	CLK Stop	Normal	See Figure 10			10	ns
t(CLKSETL)	STOPB to CLK/CLKB output settled to within 50 ps of the phase before STOPB was disabled	CLK Stop	Normal	See Figure 10			20	cycles
t _(CLKOFF)	STOPB↓ to CLK/CLKB output disabled	Normal	CLK Stop	See Figure 10			5	ns
t _(powerdown)	Delay time, PWRDNB↓ to the device in the power-down mode	Normal	Powerdown	See Figure 8			1	ms
t _(STOP)	Maximum time in CLKSTOP (STOPB = 0) before reentering normal mode (STOPB = 1)	STOPB	Normal	See Figure 10			100	μѕ
t _(ON)	Minimum time in normal mode (STOPB = 1) before reentering CLKSTOP (STOPB = 0)	Normal	CLK Stop	See Figure 10	100			ms
t(DISTLOCK)	Time from when CLK/CLKB output is settled to when the phase error between SYNCLKN and PCLKM falls within t _(phase)	Unlocked	Locked				5	ms

⁽¹⁾ All typical values are at V_{DD} = 3.3 V, T_A = 25°C.



PARAMETER MEASUREMENT INFORMATION

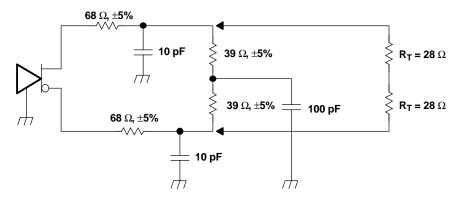
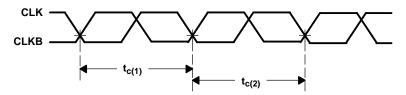
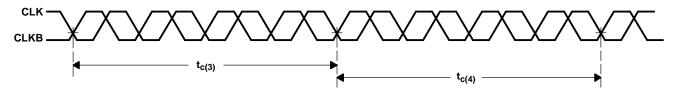


Figure 1. Test Load and Voltage Definitions ($V_{O(STOP)}$, $V_{O(X)}$, V_{O} , V_{OH} , V_{OL})



Cycle-to-cycle jitter = $|t_{c(1)} - t_{c(2)}|$ over 10000 consecutive cycles

Figure 2. Cycle-to-Cycle Jitter



Cycle-to-cycle jitter = $|t_{c(3)} - t_{c(4)}|$ over 10000 consecutive cycles

Figure 3. Short Term Cycle-to-Cycle Jitter Over Four Cycles

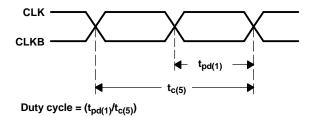


Figure 4. Output Duty Cycle



PARAMETER MEASUREMENT INFORMATION (continued)

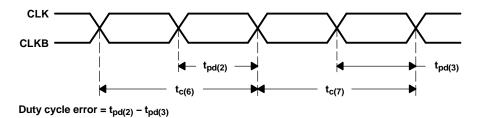


Figure 5. Duty Cycle Error (Cycle-to-Cycle)

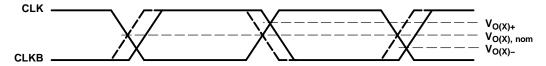


Figure 6. Crossing-Point Voltage

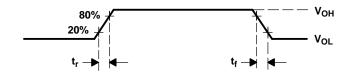


Figure 7. Voltage Waveforms

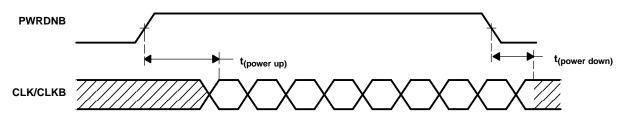


Figure 8. PWRDNB Transition Timings

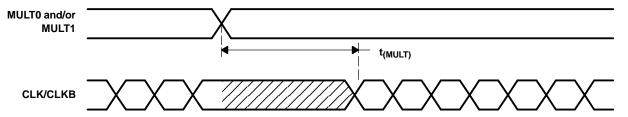
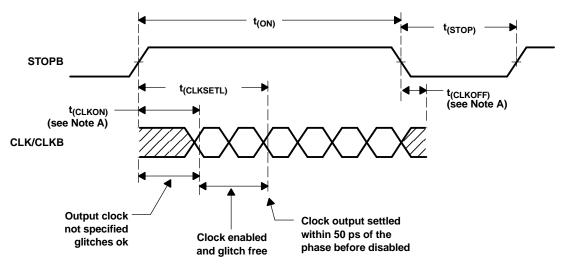


Figure 9. MULT Transition Timings



PARAMETER MEASUREMENT INFORMATION (continued)



A. $V_{ref} = V_O \pm 200 \text{ mV}$

Figure 10. STOPB Transition Timings



PACKAGE OPTION ADDENDUM

14-Sep-2018

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CDCR83ADBQR	ACTIVE	SSOP	DBQ	24	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CDCR83A	Samples
CDCR83ADBQRG4	ACTIVE	SSOP	DBQ	24	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CDCR83A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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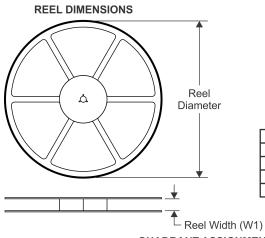


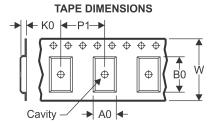
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PACKAGE MATERIALS INFORMATION

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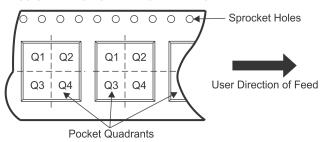
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCR83ADBQR	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

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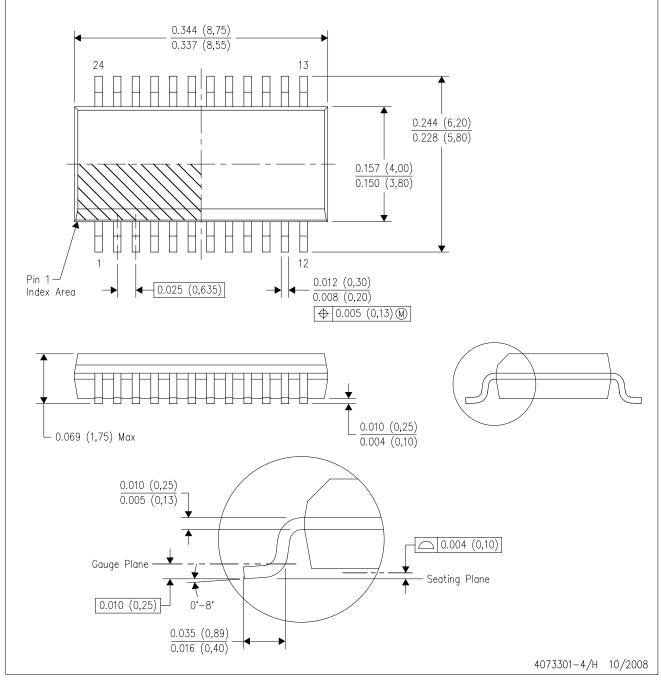


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CDCR83ADBQR	SSOP	DBQ	24	2500	367.0	367.0	38.0	

DBQ (R-PDSO-G24)

PLASTIC SMALL-OUTLINE PACKAGE



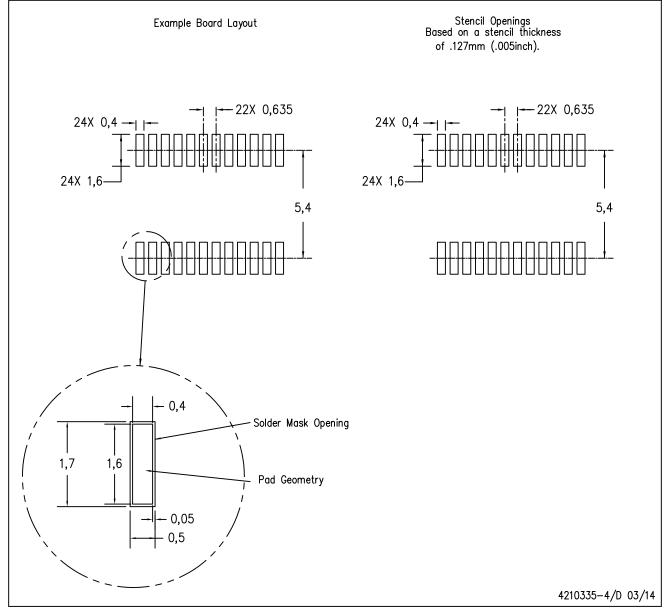
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
- D. Falls within JEDEC MO-137 variation AE.



DBQ (R-PDSO-G24)

PLASTIC SMALL OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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